FAIRCHILD SEMICONDUCTOR®

October 2013

FDP2614

N-Channel PowerTrench® MOSFET
200 V, 62 A, 27 mΩ

Features

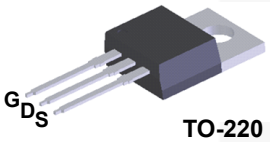
- $R_{DS(on)}$ = 22.9 mΩ (Typ.)@ V_{GS} = 10 V, I_D = 31 A
- Fast Switching Speed
- Low Gate Charge
- High Performance Trench technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handing Capability
- RoHS Compliant

General Description

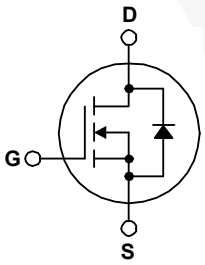
This N-Channel MOSFET is producedusing Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Consumer Appliances
- Synchronous Rectification
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies



TO-220



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter		FDP2614	Unit
V_{DS}	Drain-Source Voltage		200	V
V_{GS}	Gate-Source Voltage		± 30	V
I_D	Drain Current	- Continuous (T_C = 25°C) - Continuous (T_C = 100°C)	62 39.3	A A
I_{DM}	Drain Current	- Pulsed (Note 1)	see Figure 9	A
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	145	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
P_D	Power Dissipation	(T_C = 25°C) - Derate above 25°C	260 2.1	W W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FDP2614	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.48	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP2614	FDP2614	TO-220	Tube	N/A	50 units

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA, T_J = 25°C	200	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25°C	--	0.2	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 200V, V_{GS} = 0V V_{DS} = 200V, V_{GS} = 0V, T_J = 125°C	-- --	-- --	10 500	μA μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30V, V_{DS} = 0V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30V, V_{DS} = 0V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	3.0	4.0	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10V, I_D = 31A	--	22.9	27	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 10V, I_D = 31A	--	72	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V f = 1.0MHz	--	5435	7230	pF
C_{oss}	Output Capacitance		--	505	675	pF
C_{rss}	Reverse Transfer Capacitance		--	110	165	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 100V, I_D = 62A V_{GS} = 10V, R_{GEN} = 25Ω (Note 4)	--	77	165	ns
t_r	Turn-On Rise Time		--	284	560	ns
$t_{d(off)}$	Turn-Off Delay Time		--	103	220	ns
t_f	Turn-Off Fall Time		--	162	335	ns
Q_g	Total Gate Charge	V_{DS} = 100V, I_D = 62A V_{GS} = 10V (Note 4)	--	76	99	nC
Q_{gs}	Gate-Source Charge		--	35	--	nC
Q_{gd}	Gate-Drain Charge		--	18	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	62	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	186	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0V, I_S = 62A	--	--	1.2	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_S = 62A dI_F/dt =100A/μs	--	145	--	ns
Q_{rr}	Reverse Recovery Charge		--	0.81	--	μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 1mH, I_{AS} = 17A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 62A, di/dt ≤ 100A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

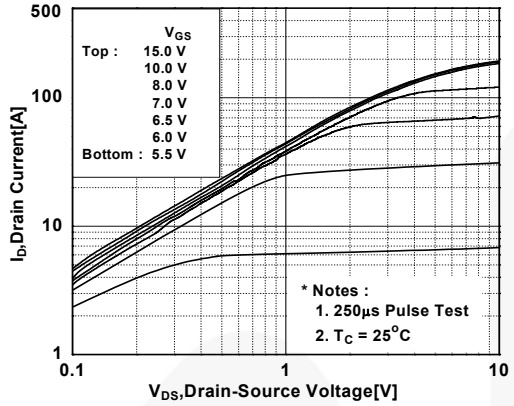


Figure 2. Transfer Characteristics

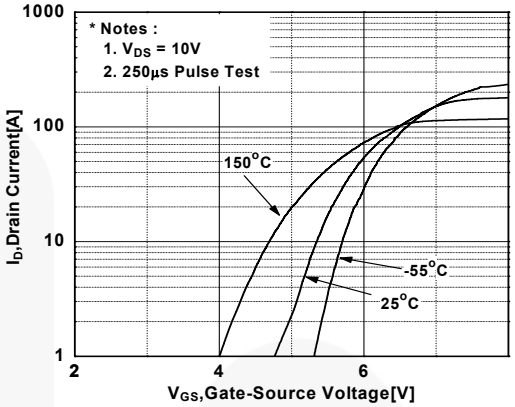


Figure3. On-Resistance Variation vs. Drain Current and Gate Voltage

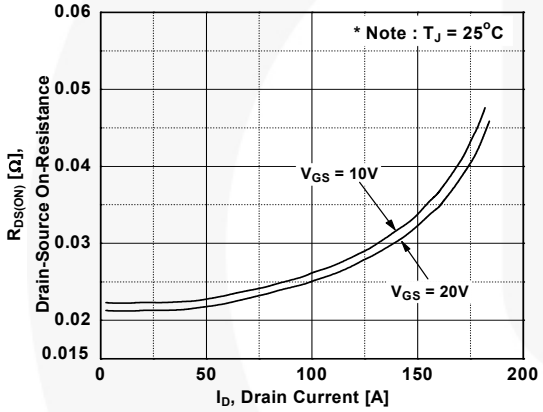


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

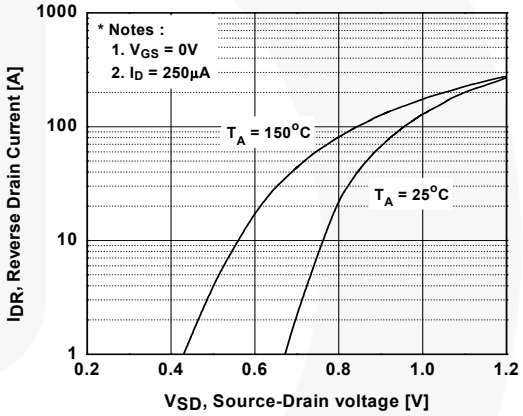


Figure 5. Capacitance Characteristics

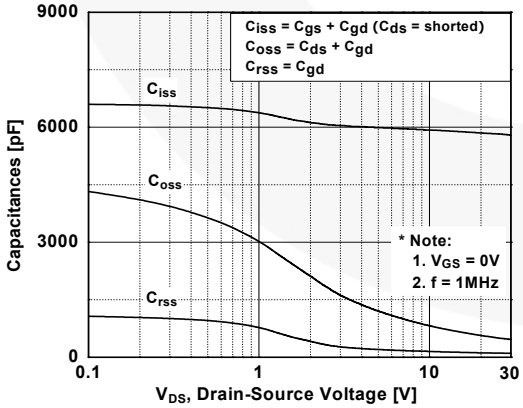
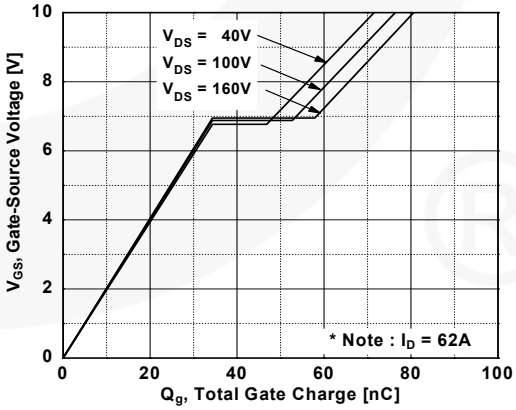


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

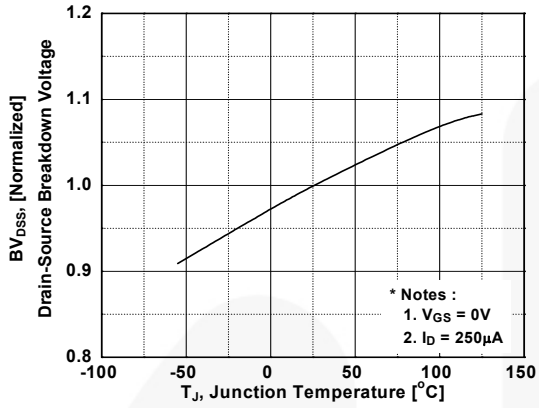


Figure 8. On-Resistance Variation vs. Temperature

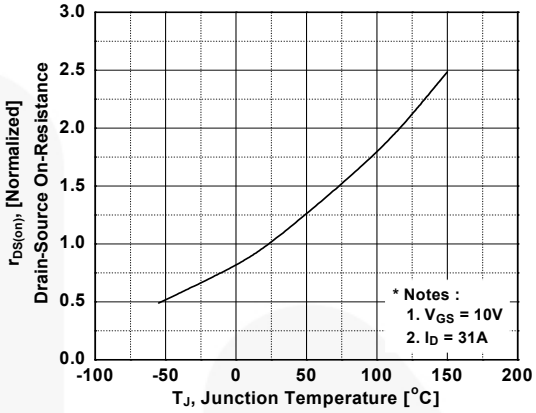


Figure 9. Maximum Safe Operating Area

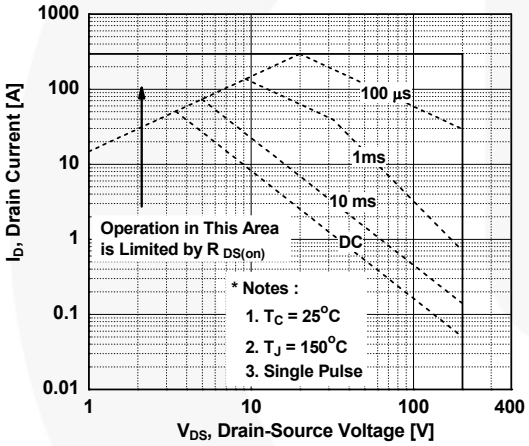


Figure 10. Maximum Drain Current vs. Case-Temperature

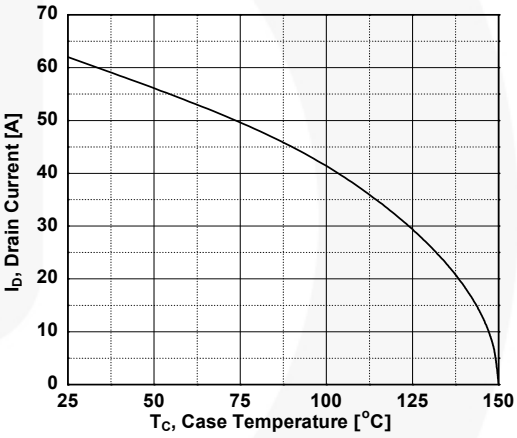


Figure 11. Transient Thermal Response Curve

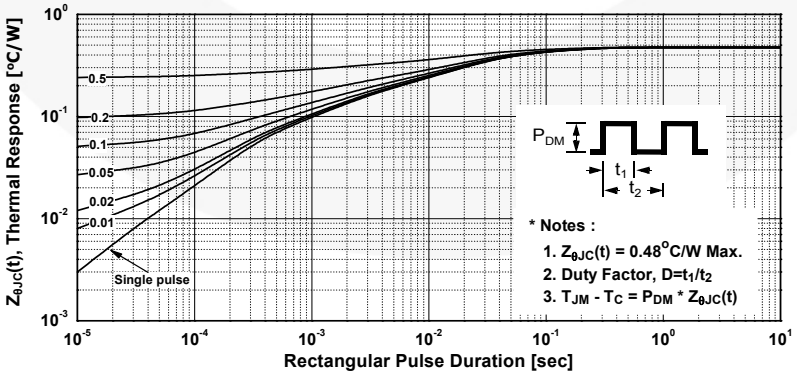


Figure 12. Gate Charge Test Circuit & Waveform

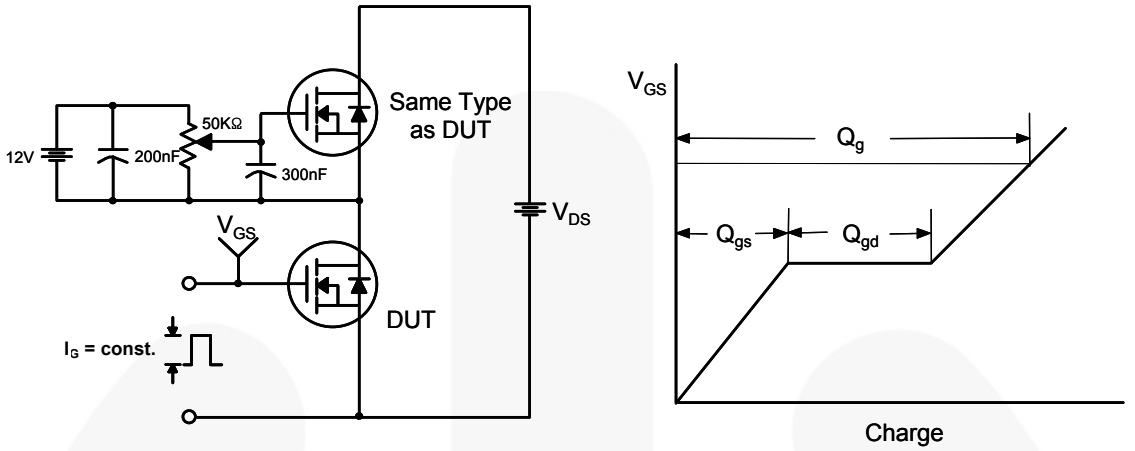


Figure 13. Resistive Switching Test Circuit & Waveforms

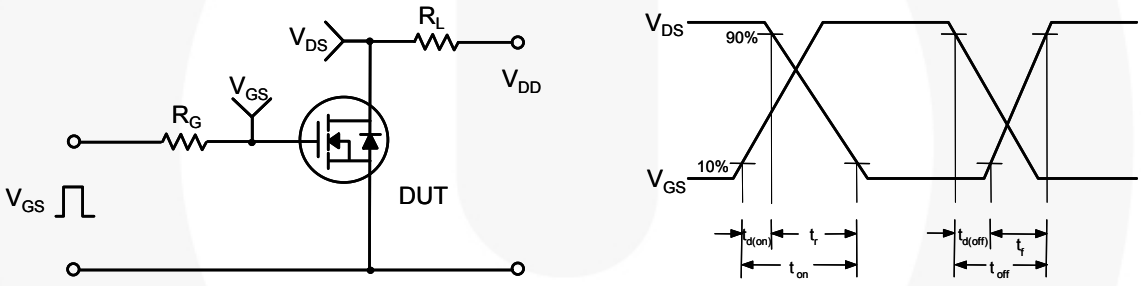


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

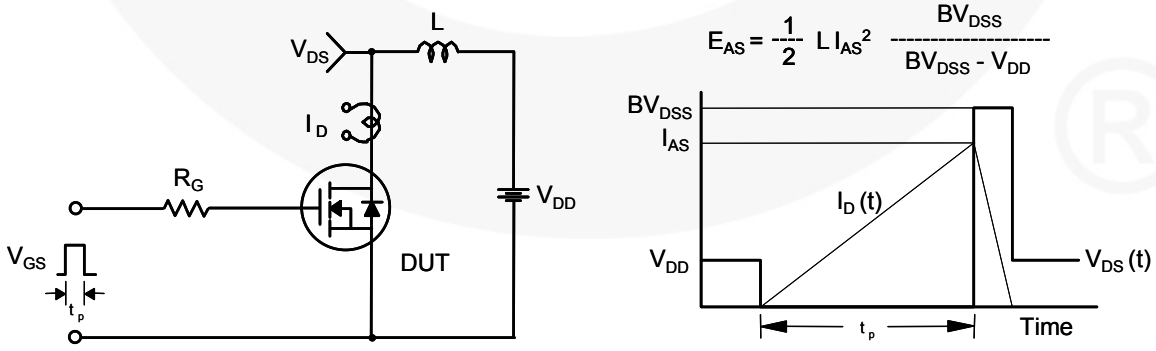
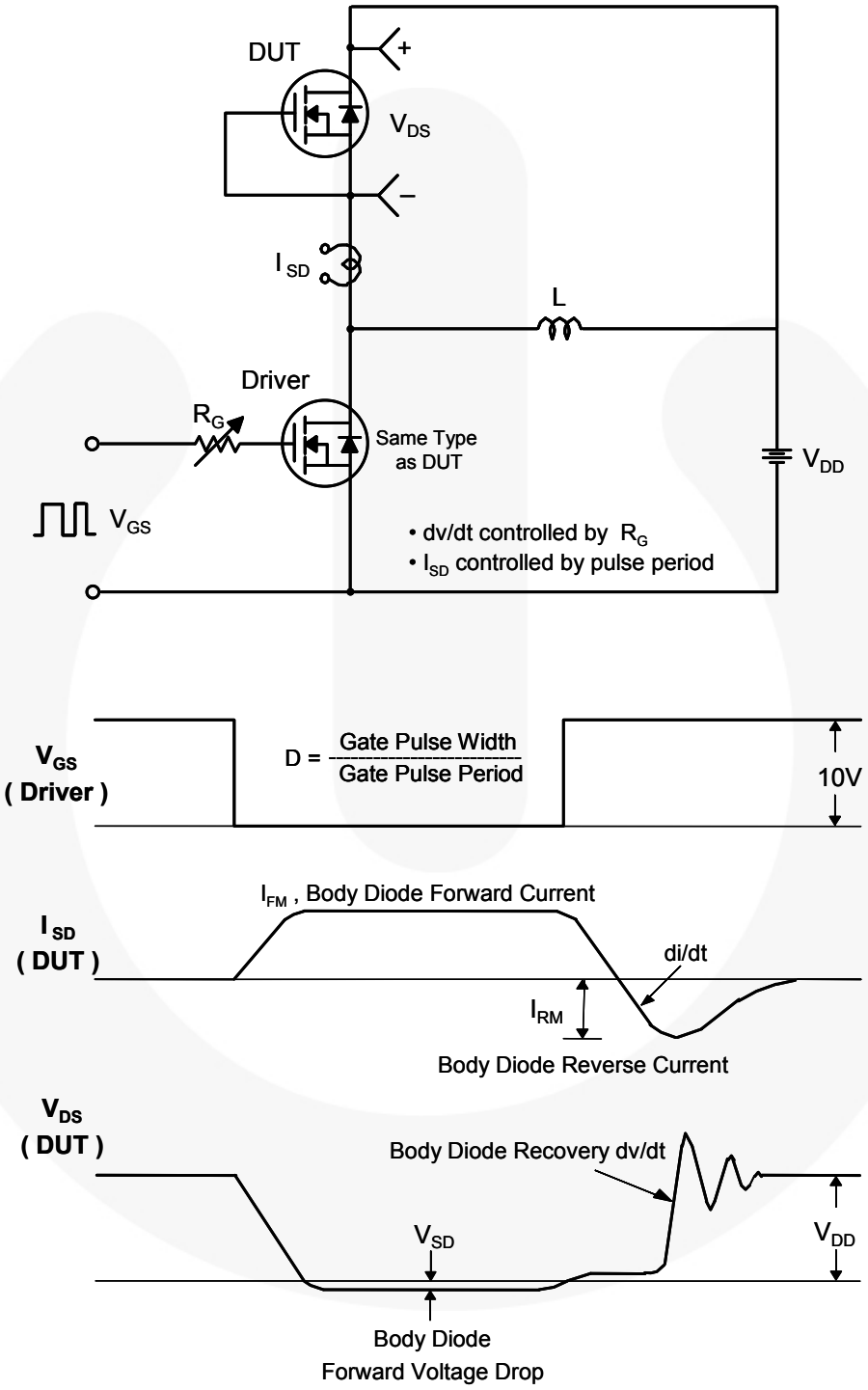


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

TO-220 3L

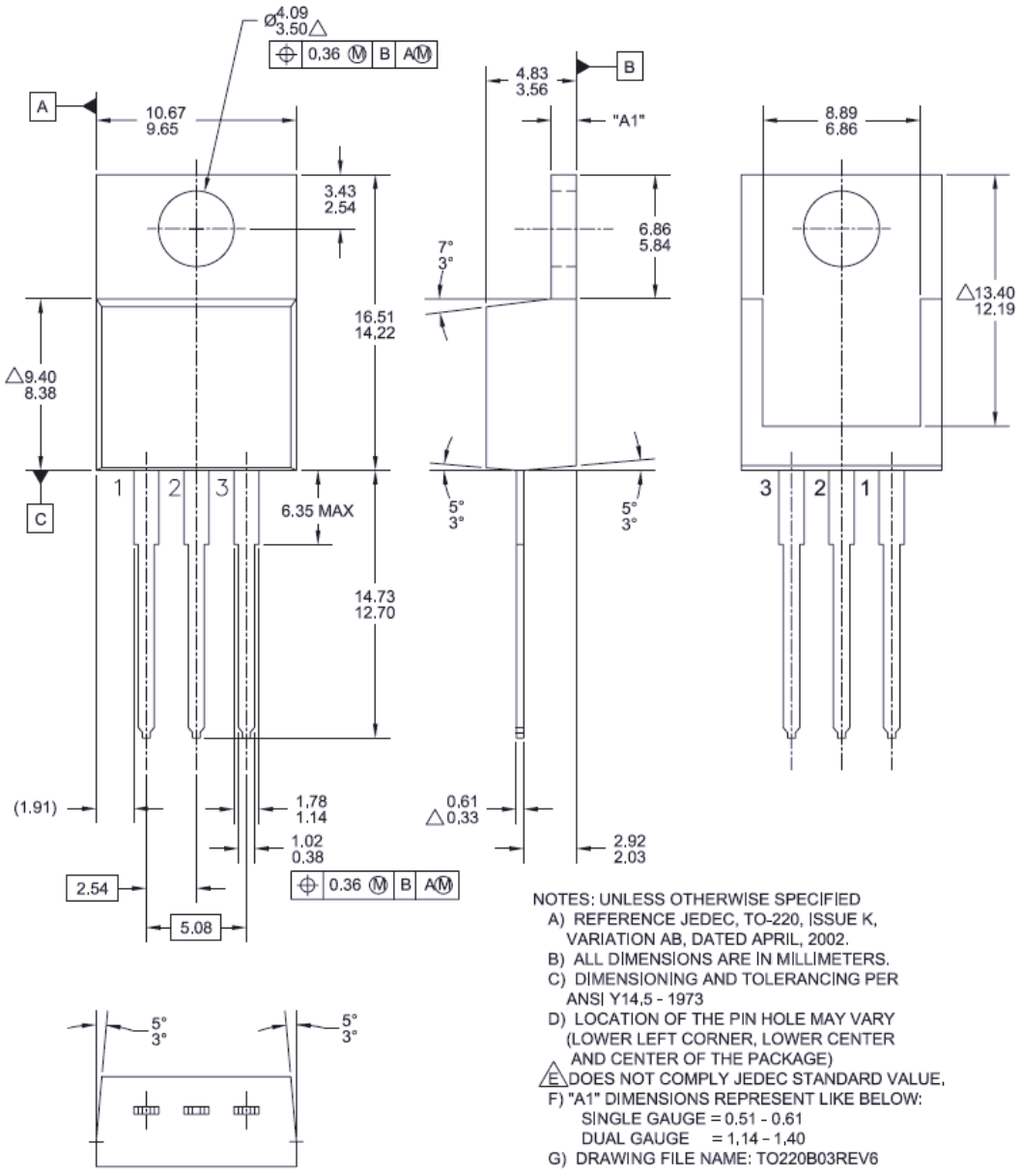


Figure 16. TO-220, Molded, 3Lead, Jedec Variation AB

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Dimension in Millimeters

FAIRCHILD SEMICONDUCTOR®

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